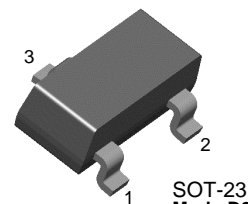


# BCW32

## NPN General Purpose Amplifier

- This device is designed for general purpose applications at collector currents to 300mA.
- Sourced from process 10.



1. Base 2. Emitter 3. Collector  
SOT-23  
Mark: D2

## Absolute Maximum Ratings \* $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	32	V
$V_{CBO}$	Collector-Base Voltage	32	V
$V_{EBO}$	Emitter-Base Voltage	5.0	V
$I_C$	Collector current (DC)	500	mA
$T_J, T_{stg}$	Operating and Storage Junction Temperature Range	-55 ~ +150	$^\circ\text{C}$

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 2.0\text{mA}, I_B = 0$	32			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10\mu\text{A}, I_B = 0$	32			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_C = 10\mu\text{A}, I_C = 0$	5.0			V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = 32\text{V}, I_E = 0$ $V_{CB} = 32\text{V}, I_E = 0, T_A = 100^\circ\text{C}$			100 10	nA $\mu\text{A}$
<b>On Characteristics</b>						
$h_{FE}$	DC Current Gain	$I_C = 2.0\text{mA}, V_{CE} = 5.0\text{V}$	200		450	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$			0.25	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 2.0\text{mA}, V_{CE} = 5.0\text{V}$	0.55		0.7	V
<b>Small Signal Characteristics</b>						
$f_T$	Current Gain Bandwidth Product	$I_C = 2.0\text{mA}, V_{CE} = 5.0\text{V}$ $f = 35\text{MHz}$	200			
$C_{obo}$	Output Capacitance	$V_{CB} = 10\text{V}, I_E = 0, f = 1.0\text{MHz}$			4.0	pF
NF	Noise Figure	$I_C = 0.2\text{mA}, V_{CE} = 5.0\text{V}$ $R_S = 2.0\text{k}\Omega, f = 1.0\text{kHz}$ $B_W = 200\text{Hz}$			10	dB

## Thermal Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Max.	Units
$P_D$	Total Device Dissipation Derate above $25^\circ\text{C}$	350 2.8	mW mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	$^\circ\text{C}/\text{W}$

Device mounted on FR-4PCB 40mm x 40mm x 1.5mm

# Typical Characteristics

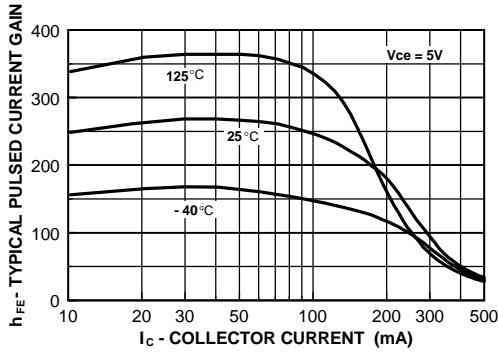


Figure 1. Typical Pulsed Current Gain vs Collector Current

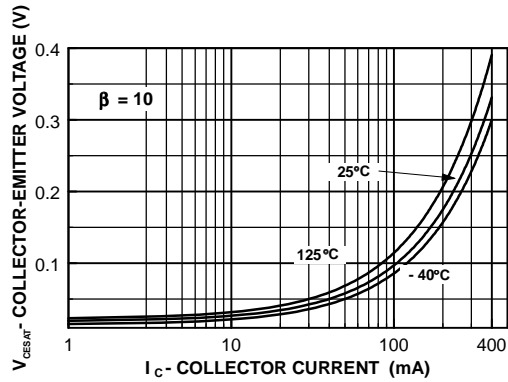


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

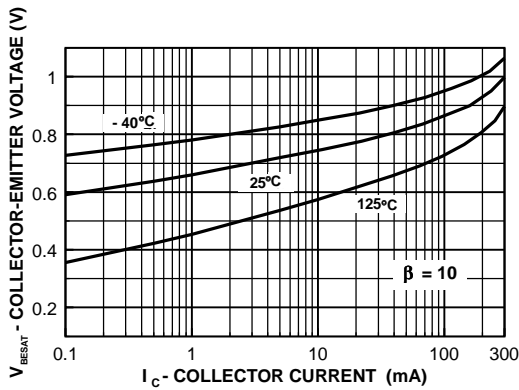


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

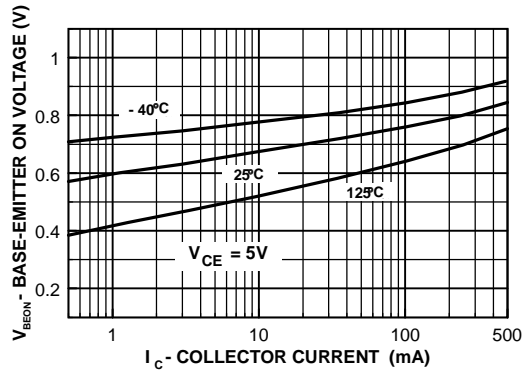


Figure 4. Base-Emitter On Voltage vs Collector Current

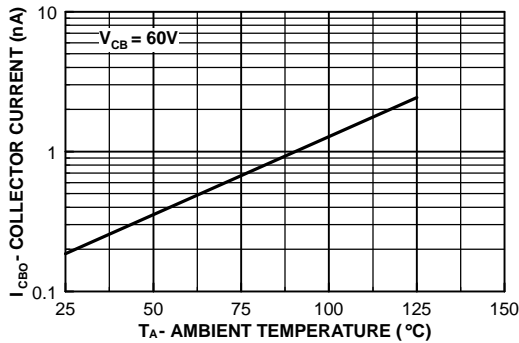


Figure 5. Collector-Cutoff Current vs Ambient Temperature

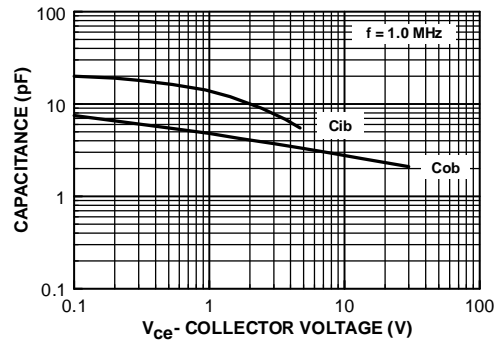


Figure 6. Input and Output Capacitance vs Reverse Voltage

# Typical Characteristics (Continued)

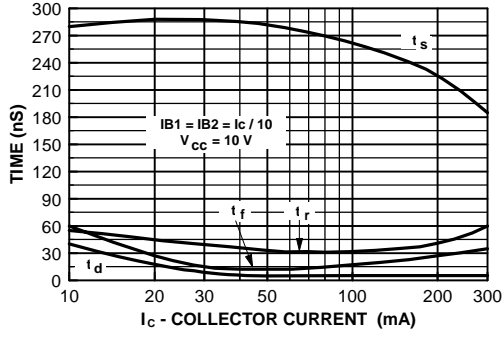


Figure 7. Switching Times vs Collector Current

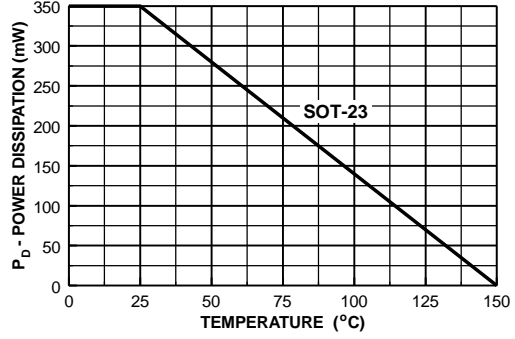
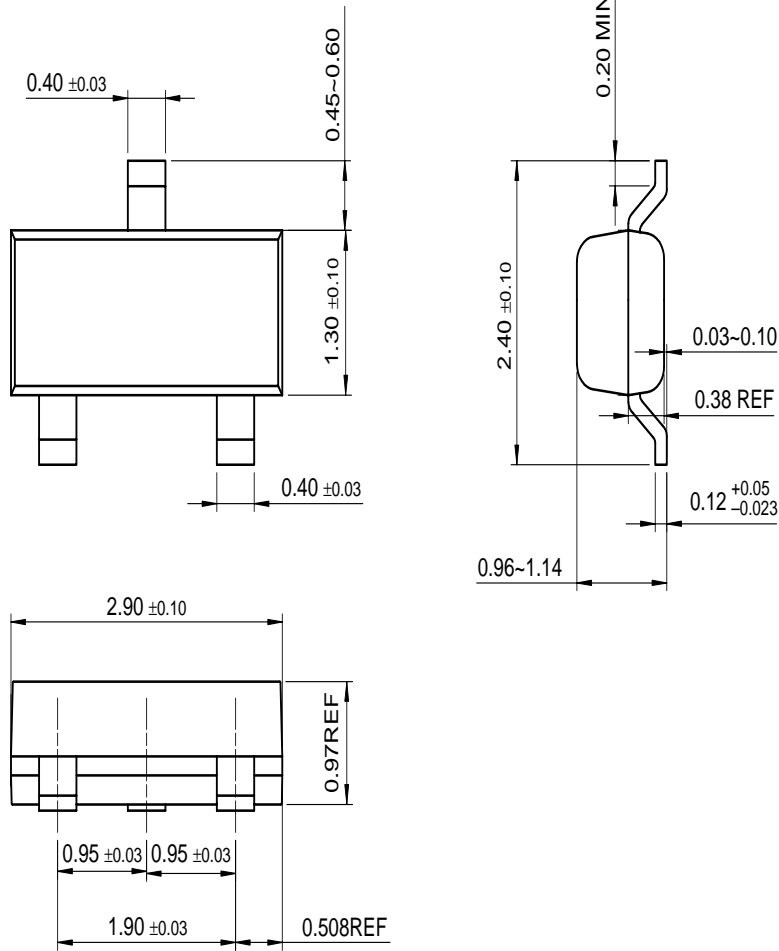


Figure 8. Power Dissipation vs Ambient Temperature

# Package Dimensions

## SOT-23



Dimensions in Millimeters

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ActiveArray <sup>™</sup>	FACT Quiet series <sup>™</sup>	ISOPLANAR <sup>™</sup>	POP <sup>™</sup>	Stealth <sup>™</sup>
Bottomless <sup>™</sup>	FAST <sup>®</sup>	LittleFET <sup>™</sup>	Power247 <sup>™</sup>	SuperSOT <sup>™</sup> -3
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The Power Franchise <sup>™</sup>		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER <sup>®</sup>	VCX <sup>™</sup>
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